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مایترونیک

فروشگاه قطعات الکترونیک

تخصص، کیفیت، قیمت مناسب

تهران - خیابان جمهوری - نرسیده به پل حافظ - پاساژ توکل - طبقه زیر همکف - پلاک B34

DATA SHEET



MOS FIELD EFFECT TRANSISTOR 2SJ598

SWITCHING P-CHANNEL POWER MOS FET

DESCRIPTION

The 2SJ598 is P-channel MOS Field Effect Transistor designed for solenoid, motor and lamp driver.

FEATURES

- Low on-state resistance:
 $R_{DS(on)1} = 130 \text{ m}\Omega \text{ MAX. (} V_{GS} = -10 \text{ V, } I_D = -6 \text{ A)}$
 $R_{DS(on)2} = 190 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -6 \text{ A)}$
- Low C_{iss} : $C_{iss} = 720 \text{ pF TYP.}$
- Built-in gate protection diode
- TO-251/TO-252 package

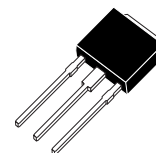
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SJ598	TO-251 (MP-3)
2SJ598-Z	TO-252 (MP-3Z)

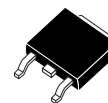
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	-60	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 12	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 30	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_T	23	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_T	1.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Single Avalanche Current ^{Note2}	I_{AS}	-12	A
Single Avalanche Energy ^{Note2}	E_{AS}	14.4	mJ

(TO-251)



(TO-252)



Notes 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

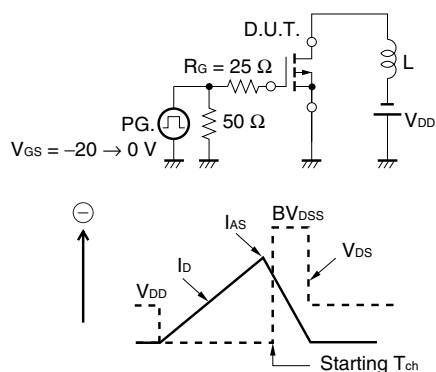
2. Starting $T_{ch} = 25^\circ\text{C}$, $V_{DD} = -30 \text{ V}$, $R_G = 25 \Omega$, $V_{GS} = -20 \rightarrow 0 \text{ V}$

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 Not all products and/or types are available in every country. Please check with an NEC Electronics sales representative for availability and additional information.

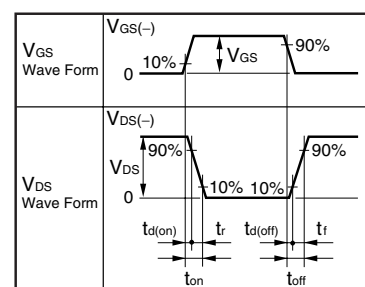
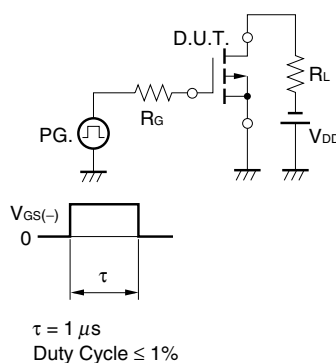
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -60 V, V _{GS} = 0 V			-10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1 mA	-1.5	-2.0	-2.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10 V, I _D = -6 A	5	11		S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = -10 V, I _D = -6 A		102	130	mΩ
	R _{DS(on)2}	V _{GS} = -4.0 V, I _D = -6 A		131	190	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V		720		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		150		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		50		pF
Turn-on Delay Time	t _{d(on)}	I _D = -6 A		7		ns
Rise Time	t _r	V _{GS} = -10 V		4		ns
Turn-off Delay Time	t _{d(off)}	V _{DD} = -30 V		35		ns
Fall Time	t _f	R _G = 0 Ω		10		ns
Total Gate Charge	Q _G	I _D = -12 A		15		nC
Gate to Source Charge	Q _{GS}	V _{DD} = -48 V		3		nC
Gate to Drain Charge	Q _{GD}	V _{GS} = -10 V		4		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 12 A, V _{GS} = 0 V		0.98		V
Reverse Recovery Time	t _{rr}	I _F = 12 A, V _{GS} = 0 V		50		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		100		nC

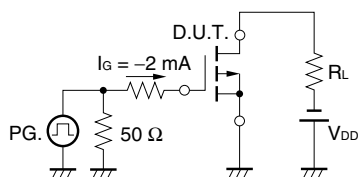
TEST CIRCUIT 1 AVALANCHE CAPABILITY



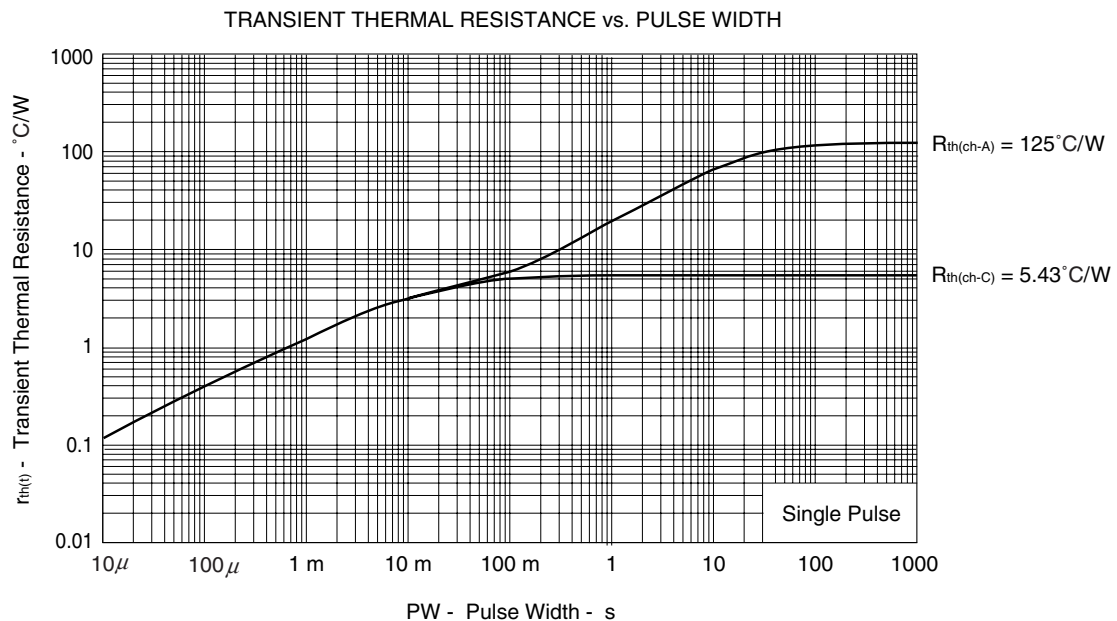
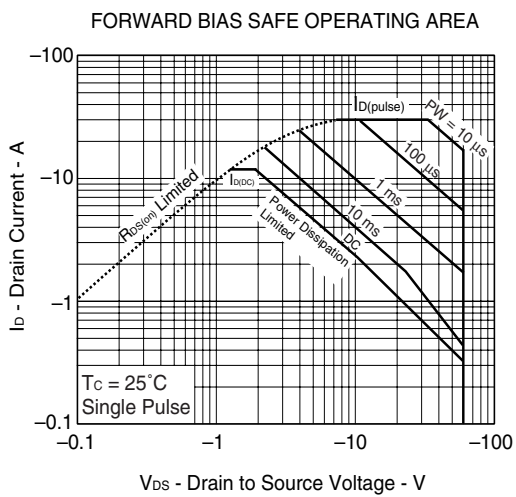
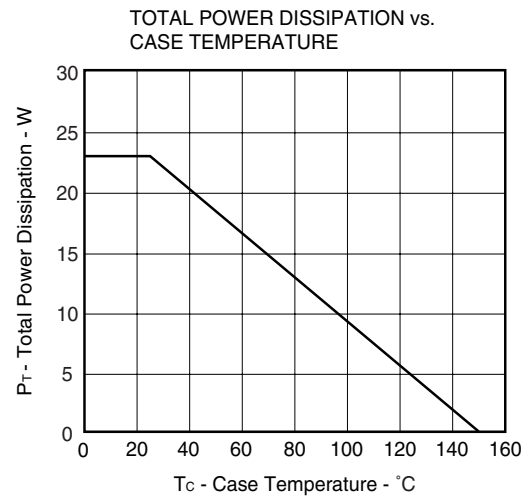
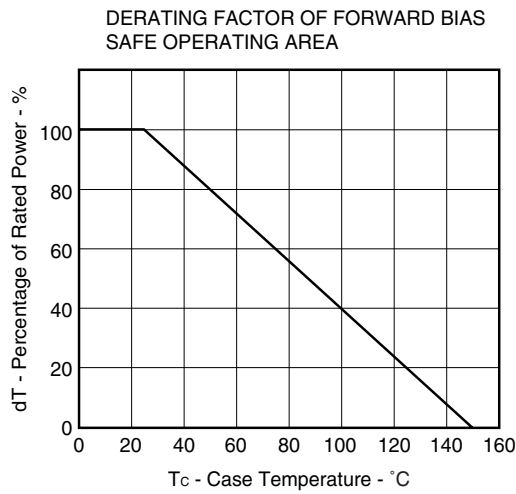
TEST CIRCUIT 2 SWITCHING TIME



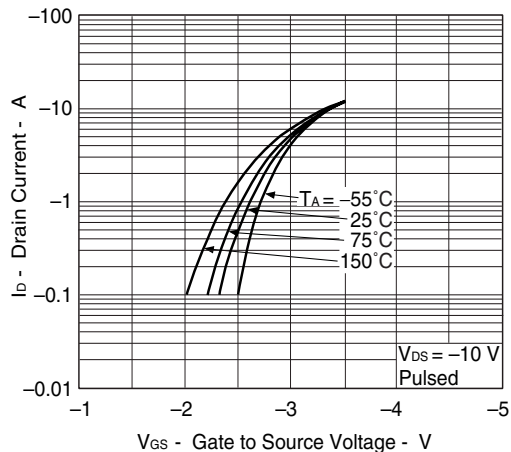
TEST CIRCUIT 3 GATE CHARGE



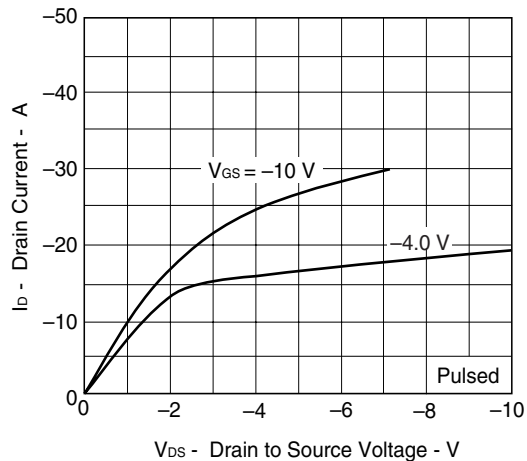
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)



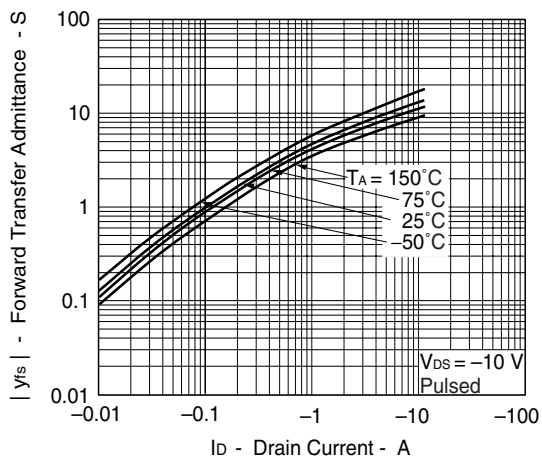
FORWARD TRANSFER CHARACTERISTICS



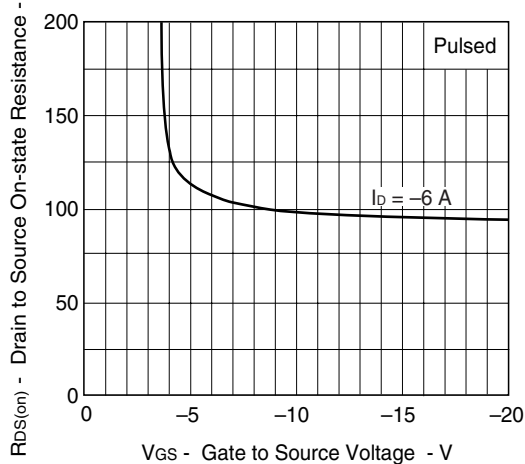
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



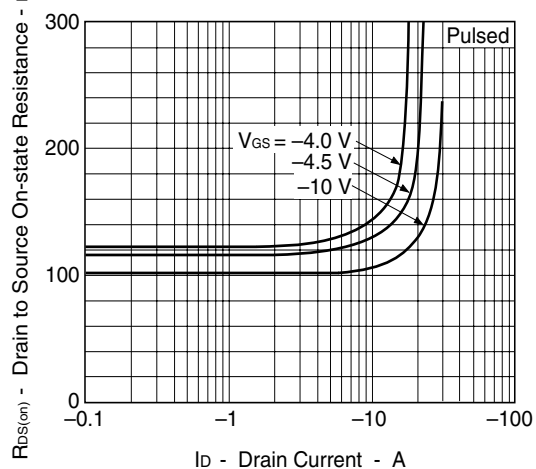
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



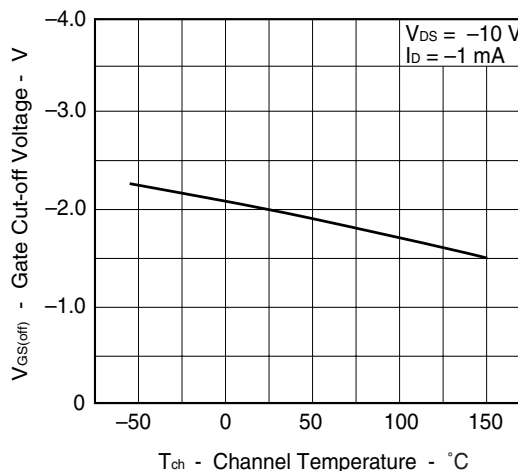
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

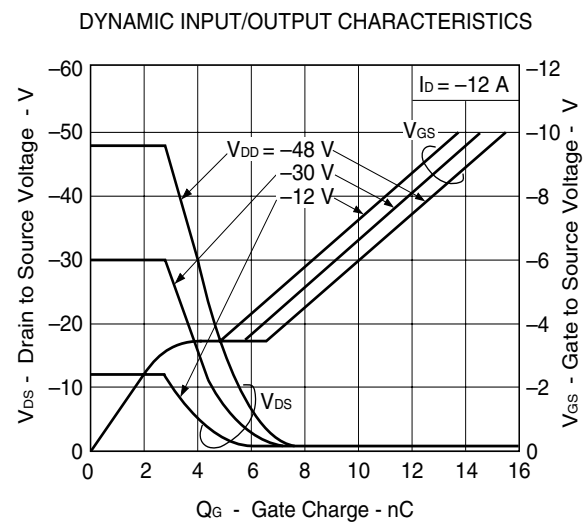
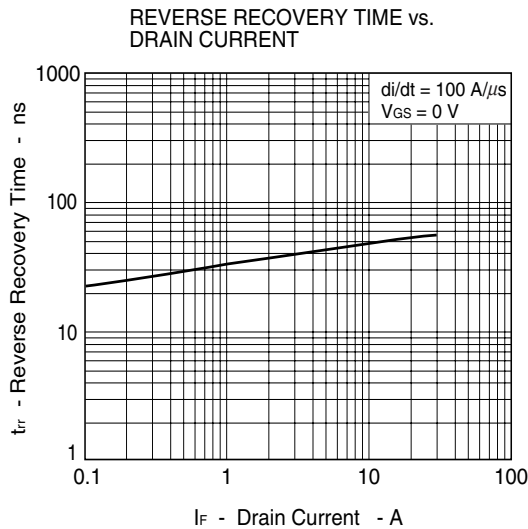
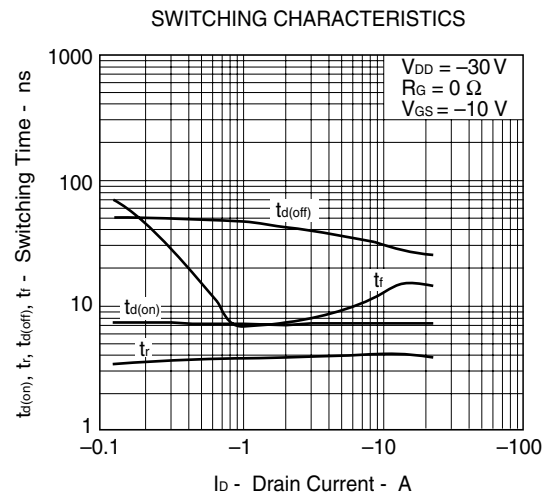
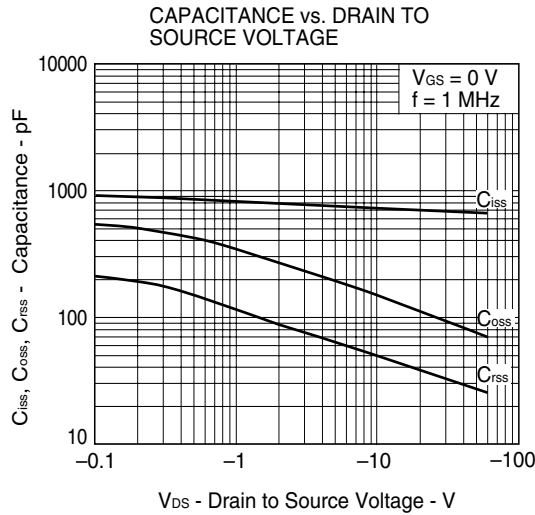
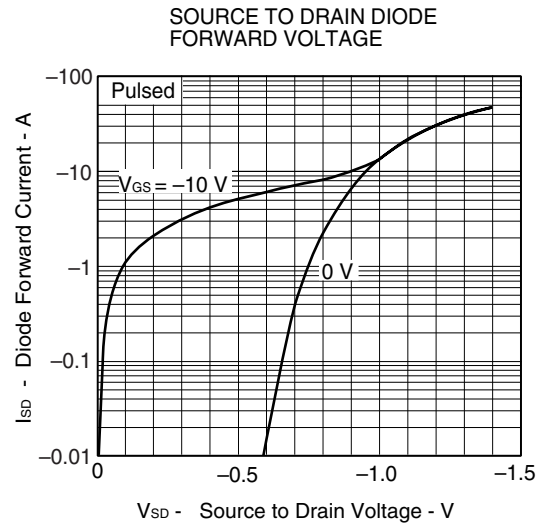
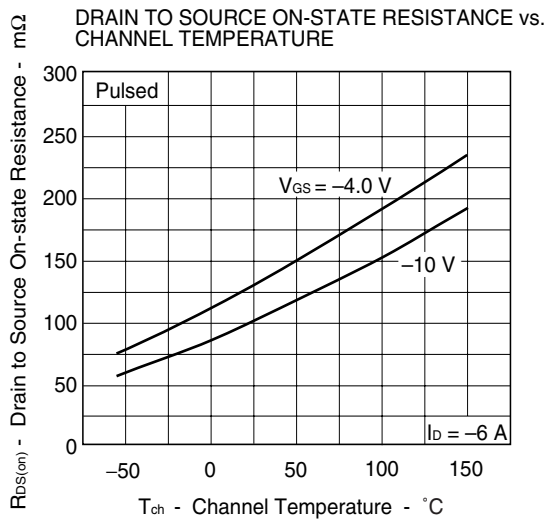


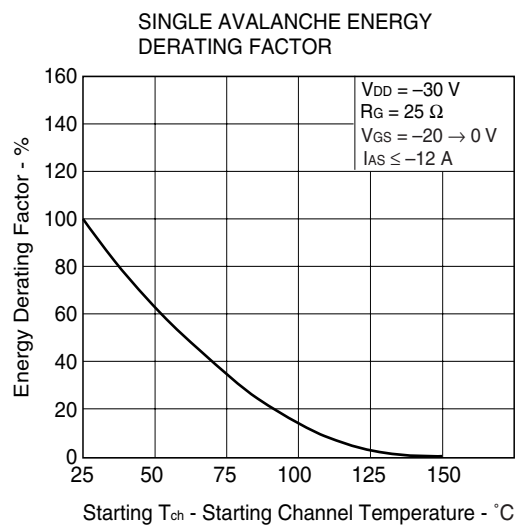
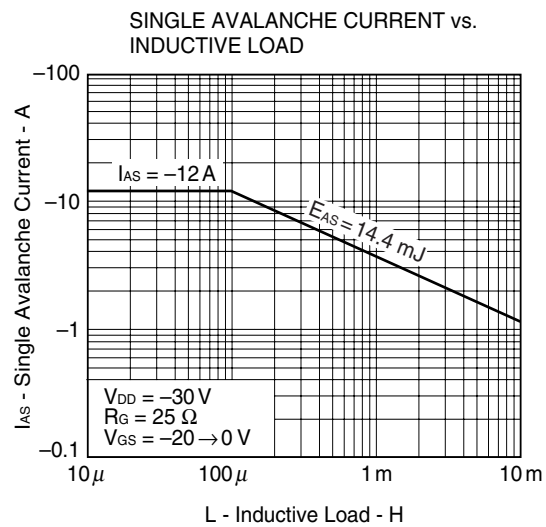
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

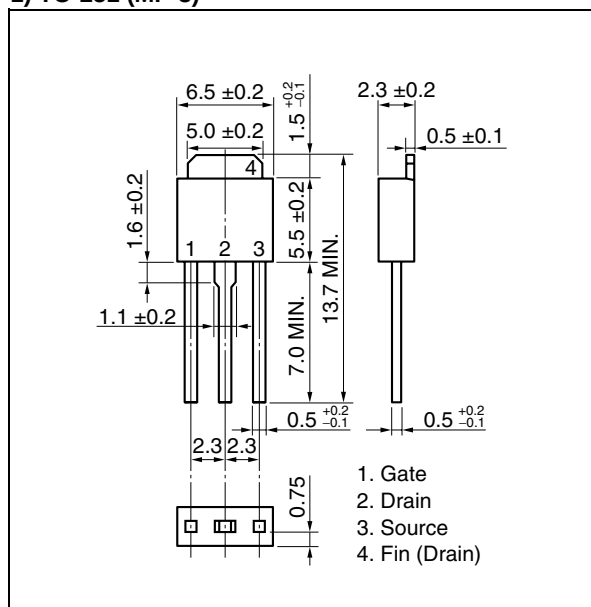




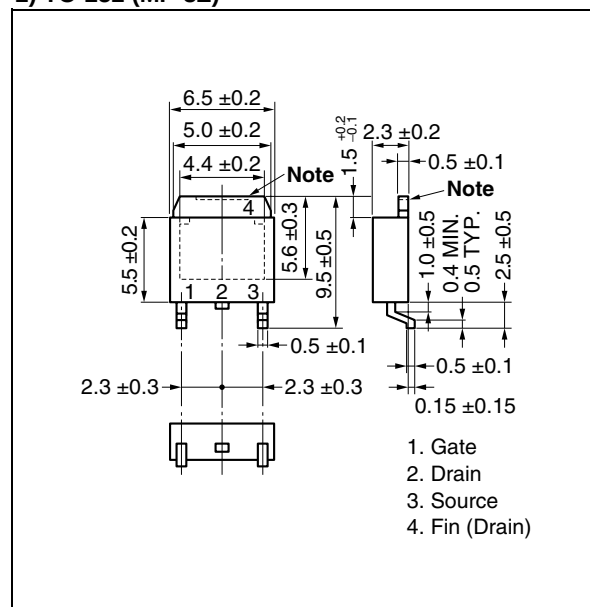


PACKAGE DRAWINGS (Unit: mm)

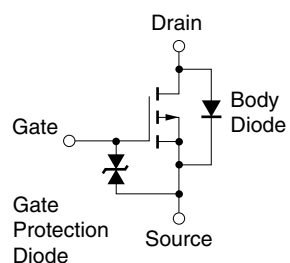
1) TO-251 (MP-3)



<R> 2) TO-252 (MP-3Z)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.